高精準性元素控制薄膜沈積系統

Deposition Process Library

- Indium oxide (InOx)

Thickness

- 15 Å ~ 100 Å

Process parameters

- Process: InOx
- Precursor: TMIn
- Oxidant: O_2 plasma (Plasma generator's power: 300 W)
- Pressure(torr): 0.1 ~ 0.3
- Carrier gas: Ar
- Purge gas: Ar
- Temperature (℃): 250 ℃
- Substrate size: 6 or 8 inch metal-free silicon wafers, or chips